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FDB031N08 N-Channel PowerTrench[®] MOSFET 75 V, 235 A, 3.1 m Ω

Features

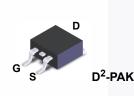
- $R_{DS(on)}$ = 2.4 m Ω (Typ.) @ V_{GS} = 10 V, I_D = 75 A
- · Fast Switching Speed
- Low Gate Charge
- High Performance Trench Technology for Extremely Low $R_{\text{DS}(\text{on})}$
- High Power and Current Handling Capability
- RoHS Compliant

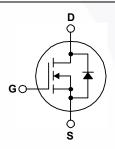
Description

This N-Channel MOSFET is produced using Fairchild Semiconductor's advanced PowerTrench[®] process that has been tailored to minimize the on-state resistance while maintaining superior switching performance.

Applications

- Synchronous Rectification for ATX / Server / Telecom PSU
- Battery Protection Circuit
- Motor Drives and Uninterruptible Power Supplies





MOSFET Maximum Ratings T_C = 25°C unless otherwise noted.

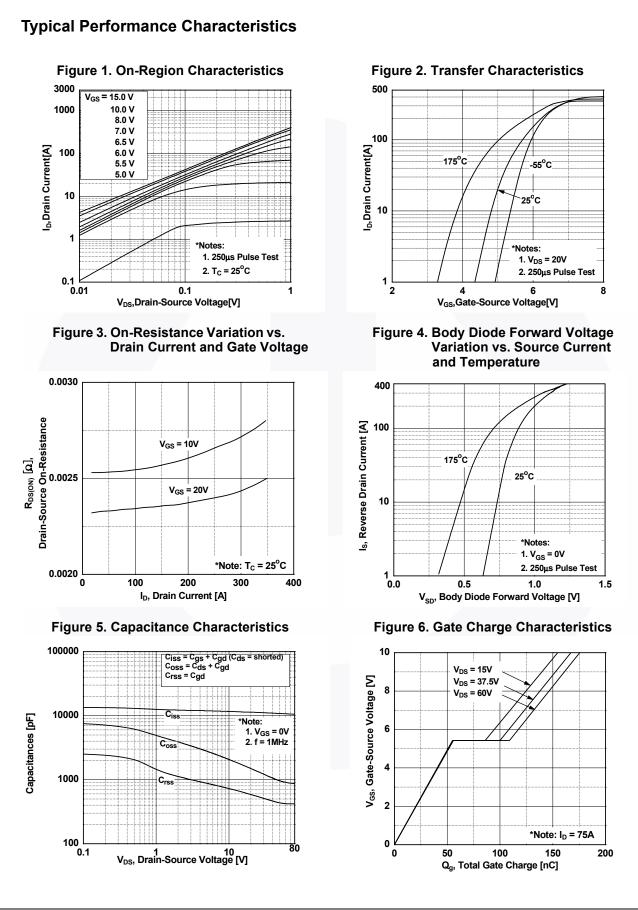
Symbol		Parameter		FDB031N08	Unit
V _{DSS}	Drain to Source Voltage			75	V
V _{GSS}	Gate to Source Voltage		±20	V	
	Drain Current - Continuous (T _C = 25 ^o C, Silicon Limited) - Continuous (T _C = 100 ^o C, Silicon Limited)			235	Α
ID				165	A
	-	Continuous (T _C = 25 ^o C, Pack	age Limited)	120	Α
I _{DM}	Drain Current	- Pulsed	(Note 1)	940	А
E _{AS}	Single Pulsed Avalanche Energy		(Note 2)	1995	mJ
dv/dt	Peak Diode Recovery dv/dt		(Note 3)	5.5	V/ns
P _D	Dower Dissinction	(T _C = 25 ^o C)		375	W
	Power Dissipation	- Derate Above 25°C	- Derate Above 25°C		W/ºC
T _J , T _{STG}	Operating and Storage Temperature Range			-55 to +175	°C
ΤL	Maximum Lead Temperate	ure for Soldering, 1/8" from Case	for 5 Seconds	300	°C

Thermal Characteristics

Symbol	Parameter	FDB031N08	Unit
$R_{ extsf{ heta}JC}$	Thermal Resistance, Junction to Case, Max.	0.4	°C/W
$R_{ extsf{ heta}JA}$	Thermal Resistance, Junction to Ambient, Max.	62.5	0/00

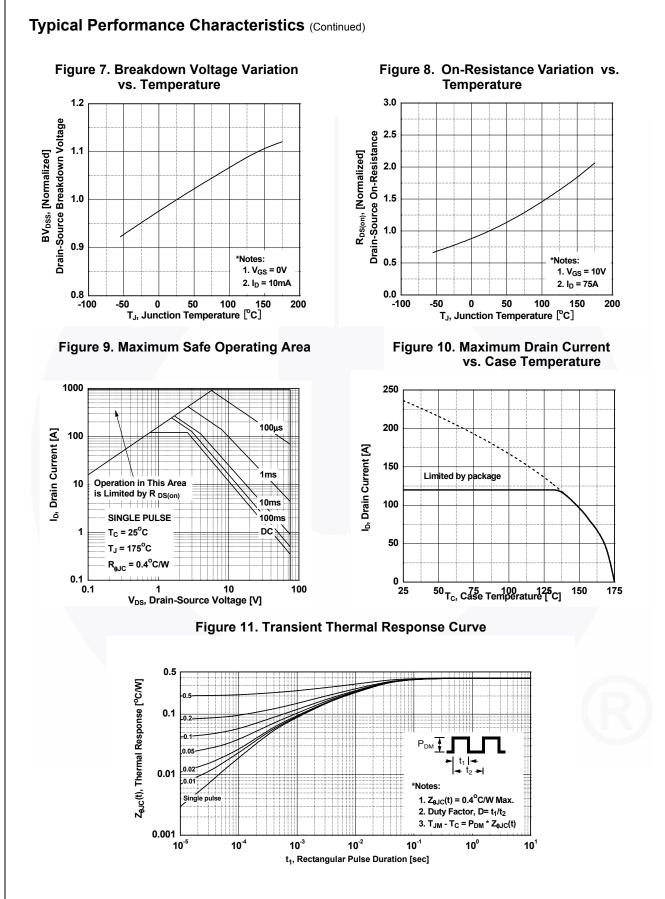
November 2013

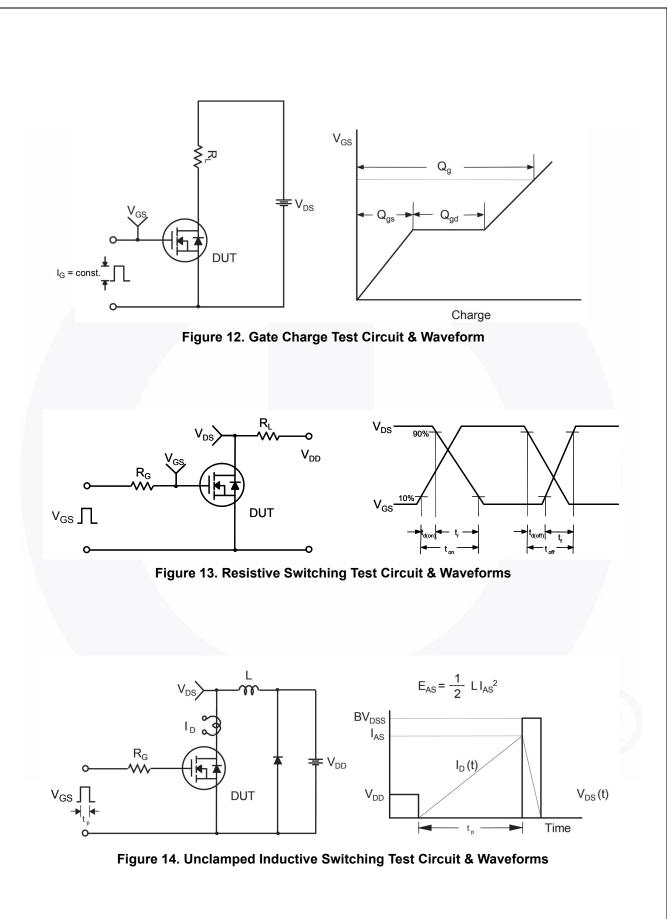
B FDB031N08 Characteristics T _C = 2 Parameter Fistics rain to Source Breakdown Volt	D ² -PA	s otherwise noted	Reel	330 mm	Min.	4 mm Typ.	800 Max.	units
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Parameter istics		-			Min.	Тур.	Max.	Unit
								I
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				-			pF	
							nC	
		V _{DS} = 60 V, I _D = 75 A, V _{GS} = 10 V (Note 4)		-		-	nC	
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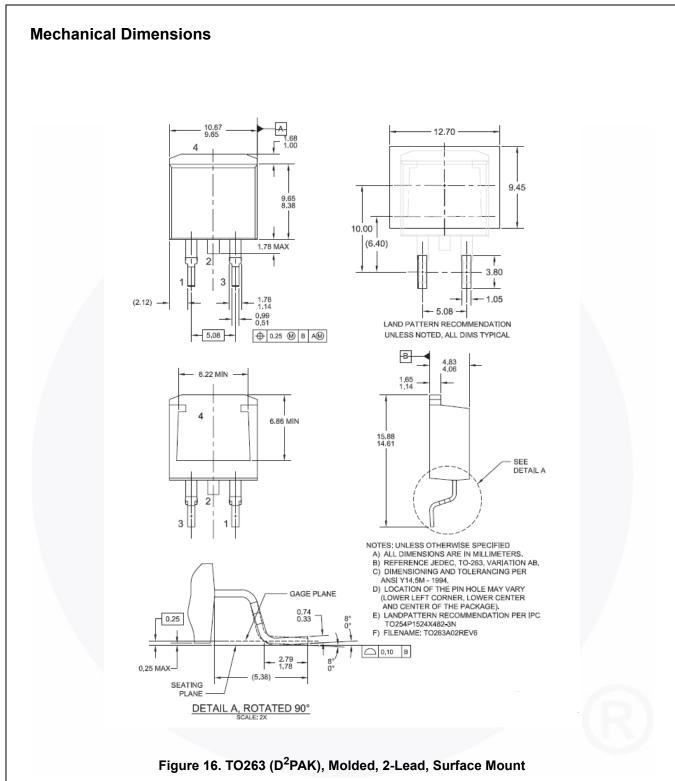


FDB031N08 — N-Channel PowerTrench[®] MOSFET

DUT + V_{DS} a ۱_{SD} م L Driver R_G, Same Type as DUT L F ∨_{DD} $\prod V_{GS}$ • dv/dt controlled by R_{G} • I_{SD} controlled by pulse period Î Gate Pulse Width V_{GS} D = Gate Pulse Period 10V (Driver) I_{FM}, Body Diode Forward Current I _{SD} di/dt (DUT) I_{RM} Body Diode Reverse Current V_{DS} (DUT) Body Diode Recovery dv/dt V_{SD} V_{DD} Body Diode Forward Voltage Drop Figure 15. Peak Diode Recovery dv/dt Test Circuit & Waveforms

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FDB031N08 — N-Channel PowerTrench[®] MOSFET



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Dual Cool™	Marking Small Speakers Sound Lo		TinyPWM™
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No Identification Needed	Full Production	Datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve the design.
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- Лицензия ФСБ на осуществление работ с использованием сведений, составляющих государственную тайну;
- Поставка специализированных компонентов (Xilinx, Altera, Analog Devices, Intersil, Interpoint, Microsemi, Aeroflex, Peregrine, Syfer, Eurofarad, Texas Instrument, Miteq, Cobham, E2V, MA-COM, Hittite, Mini-Circuits, General Dynamics и др.);

Помимо этого, одним из направлений компании «ЭлектроПласт» является направление «Источники питания». Мы предлагаем Вам помощь Конструкторского отдела:

- Подбор оптимального решения, техническое обоснование при выборе компонента;
- Подбор аналогов;
- Консультации по применению компонента;
- Поставка образцов и прототипов;
- Техническая поддержка проекта;
- Защита от снятия компонента с производства.



Как с нами связаться

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